



2SB1132

PNP SILICON TRANSISTOR

MEDIUM POWER TRANSISTOR

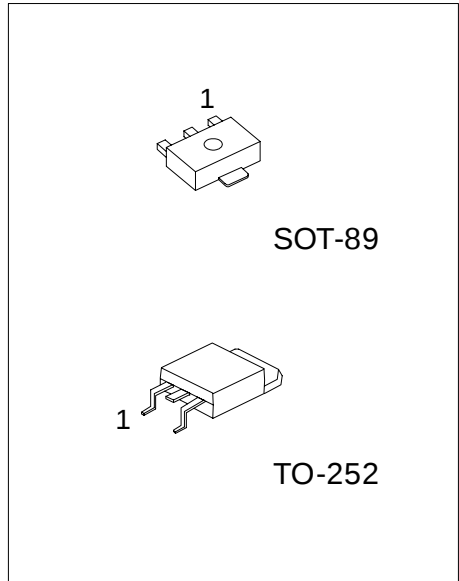
DESCRIPTION

The UTC 2SB1132 is a epitaxial planar type PNP silicon transistor.

FEATURES

* Low $V_{CE(SAT)}$.

$V_{CE(SAT)} = -0.2V(Typ.) (I_C/I_B = -500mA/-50mA)$



*Pb-free plating product number: 2SB1132L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SB1132-x-AB3-R	2SB1132L-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB1132-x-TN3-R	2SB1132L-x-TN3-R	TO-252	B	C	E	Tape Reel
2SB1132-x-TN3-T	2SB1132L-x-TN3-T	TO-252	B	C	E	Tube

2SB1132L-x-AB3-R	(1)Packing Type	(1) R: Tape Reel, T: Tube
	(2)Package Type	(2) AB3: SOT-89, TN3: TO-252
	(3)Rank	(3) x: refer to Classification of h_{FE}
	(4)Lead Plating	(4) L: Lead Free Plating, Blank: Pb/Sn

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	DC	-1	A
Collector Current (Single pulse, Pw=100ms)	PULSE		
Collector Power Dissipation	SOT-89	0.5	W
	TO-252	1	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

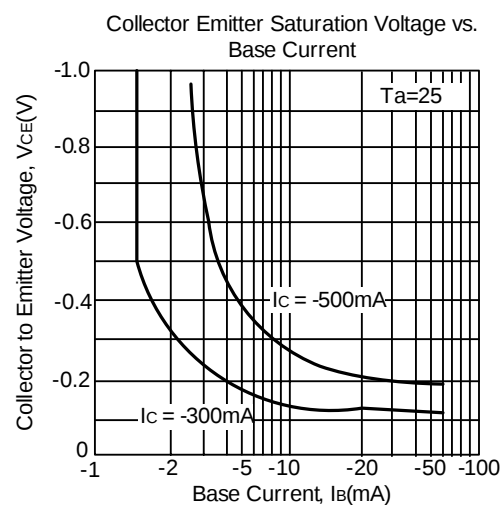
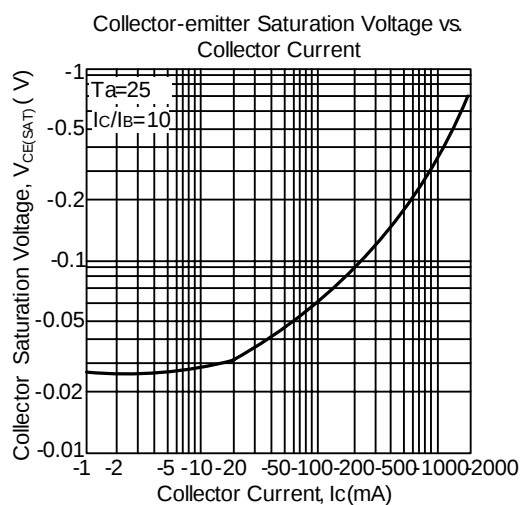
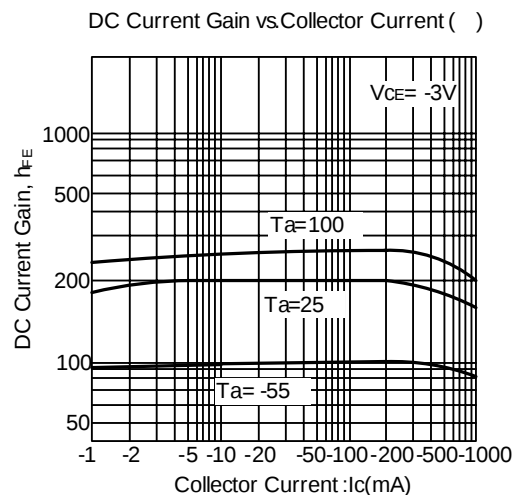
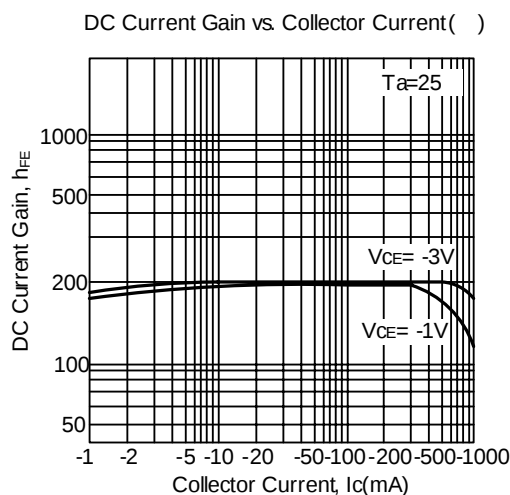
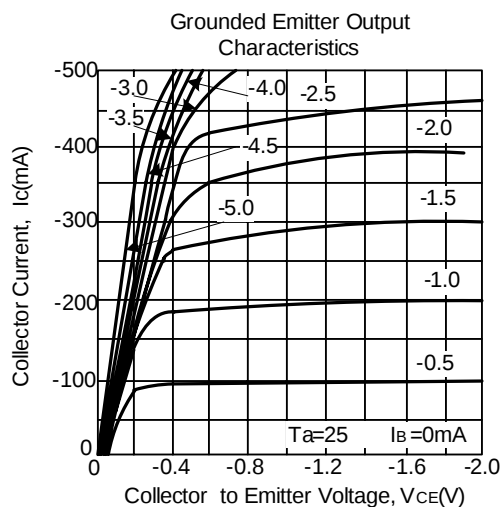
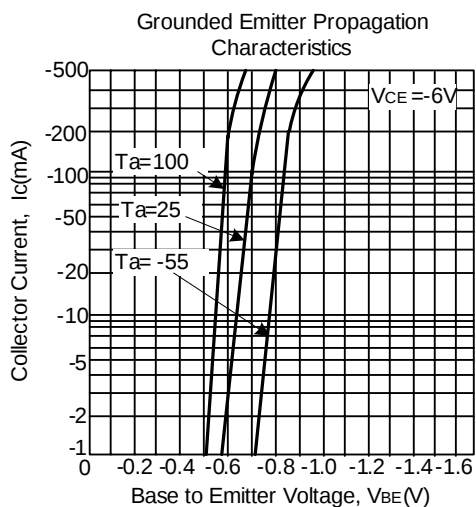
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV_{CBO}	$I_C = -50\mu A$	-40			V
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA$	-32			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = -50\mu A$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -20V$			-0.5	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4V$			-0.5	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500mA, I_B = -50mA$ (Note)		-0.2	-0.5	V
DC Current Transfer Ratio	h_{FE}	$V_{CE} = -3V, I_C = -0.1A$ (Note)	82		390	
Transition Frequency	f_T	$V_{CE} = -5V, I_E = 50mA, f = 30MHz$		150		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		20	30	pF

Note: Measured using pulse current.

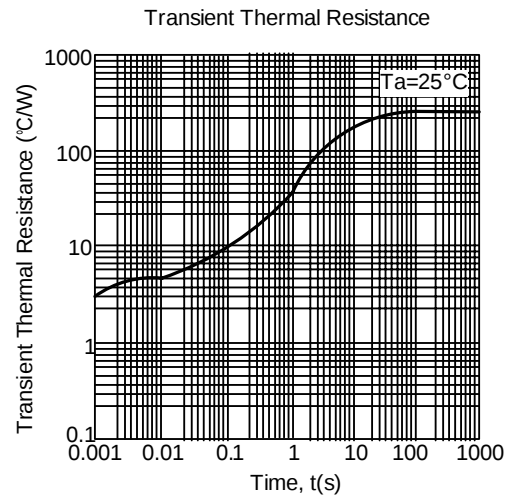
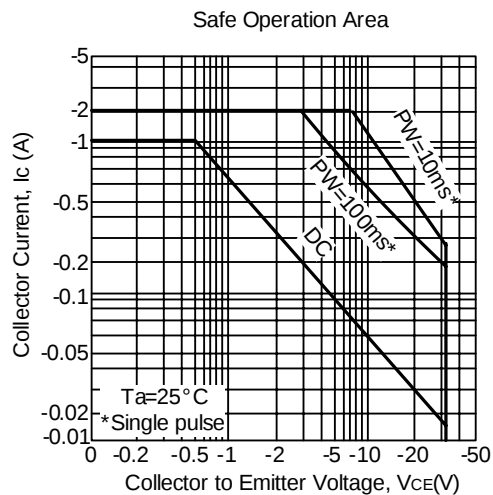
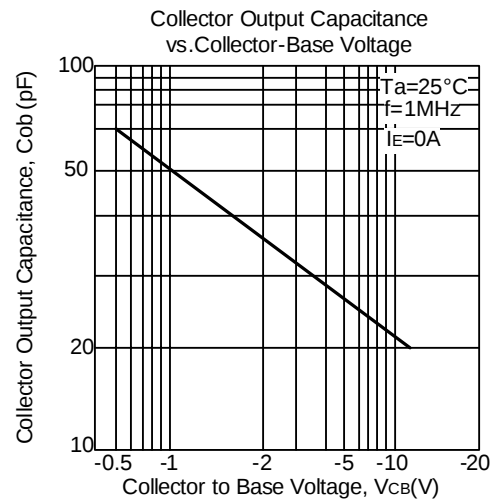
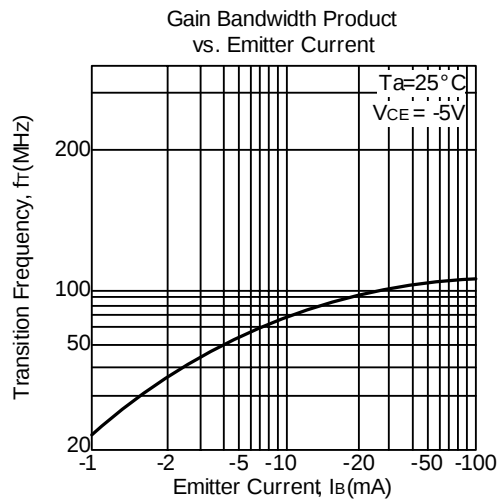
■ CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82-180	120-270	180-390

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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